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(54) **SLEW-RATE CONTROL APPARATUS AND METHODS FOR A POWER TRANSISTOR TO REDUCE VOLTAGE TRANSIENTS DURING INDUCTIVE FLYBACK**

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H03K 3/00 (2006.01)

(52) **U.S. Cl.** **327/170; 327/110**

(58) **Field of Classification Search** None
See application file for complete search history.

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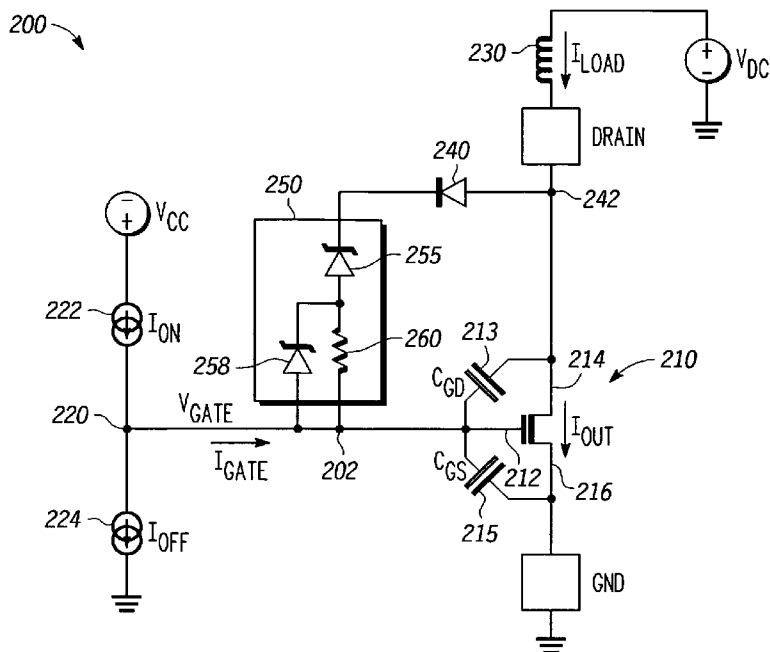
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(57) **ABSTRACT**

Apparatus and methods that reduce the amount of conducted/radiated emissions from a power switch (200) when a transistor (210) is switched OFF are disclosed. In addition, apparatus and methods that reduce the slew rate in a power switch when the power switch is switched off are disclosed. The apparatus comprises a transistor (210) including an inductive load (230) coupled to the transistor, a plurality of current sources (222, 224) coupled to the gate of the transistor, and a clamp (250) coupled to either the gate and the drain of the transistor, or to the gate and to ground depending on the location of the inductive load, wherein the clamp comprises a resistive element (260) to increase the voltage of the clamp when current flows through the clamp, and wherein the increased voltage causes the apparatus to include a different slew rate.

16 Claims, 6 Drawing Sheets



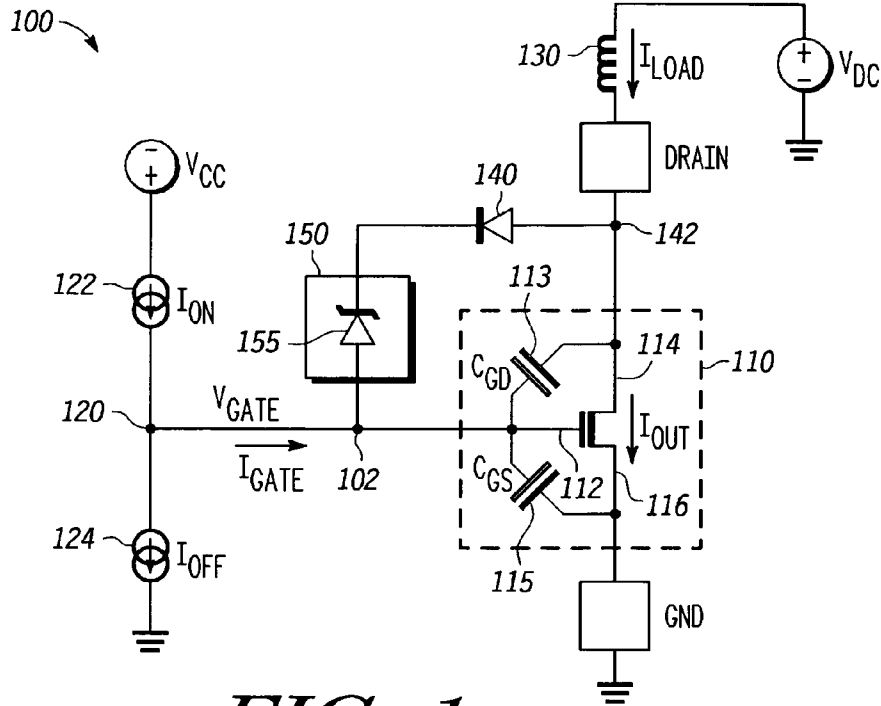


FIG. 1
-PRIOR ART-

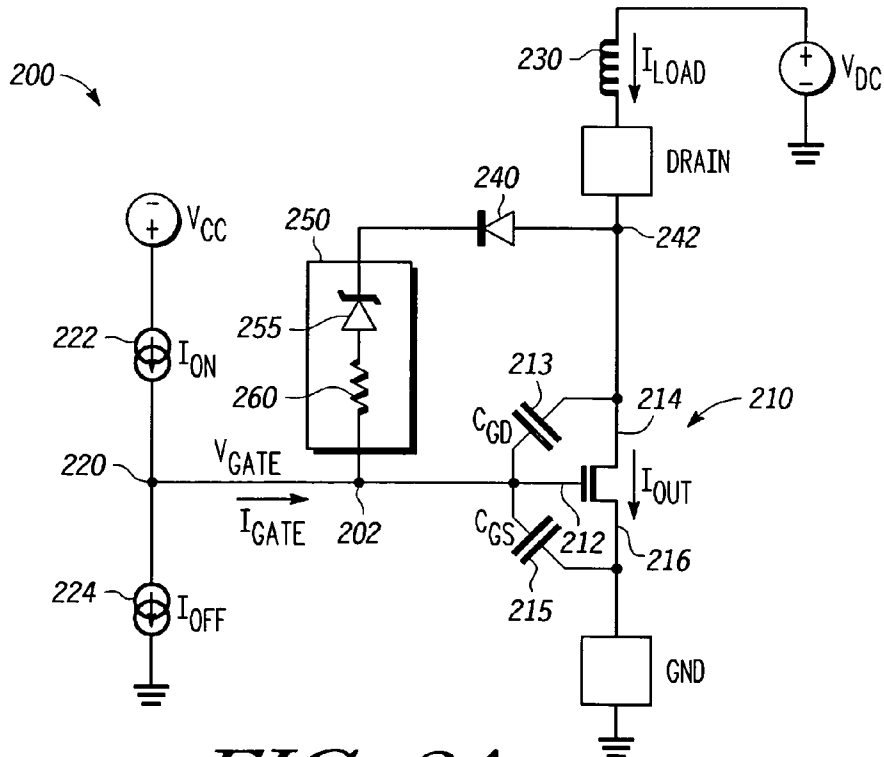


FIG. 2A

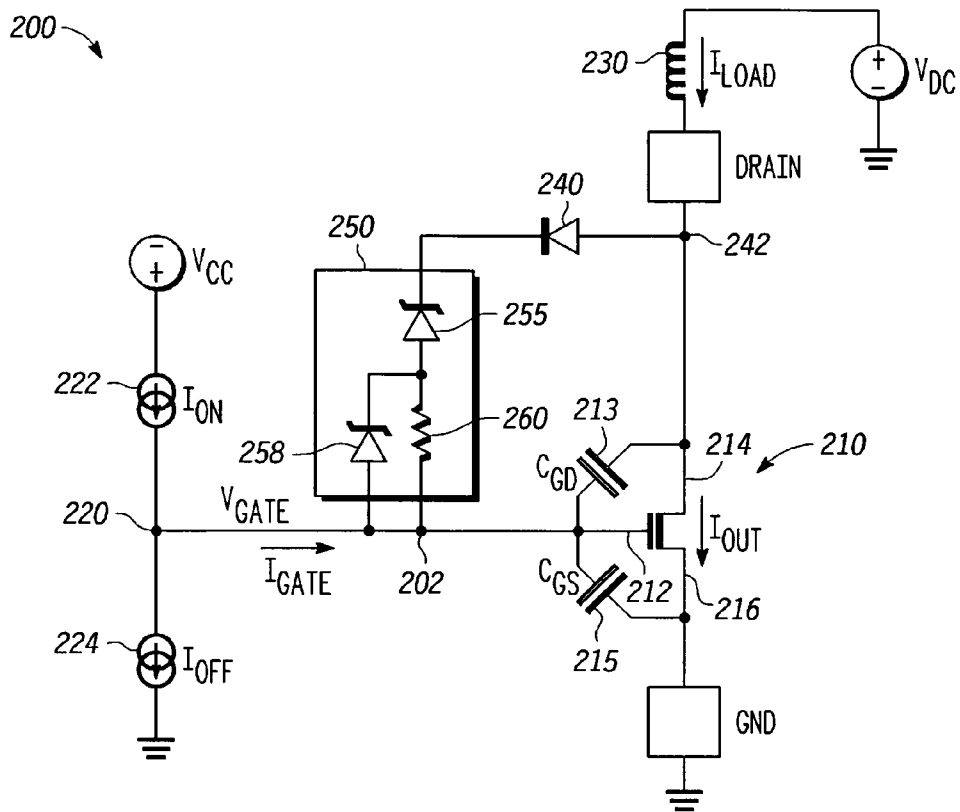


FIG. 2B

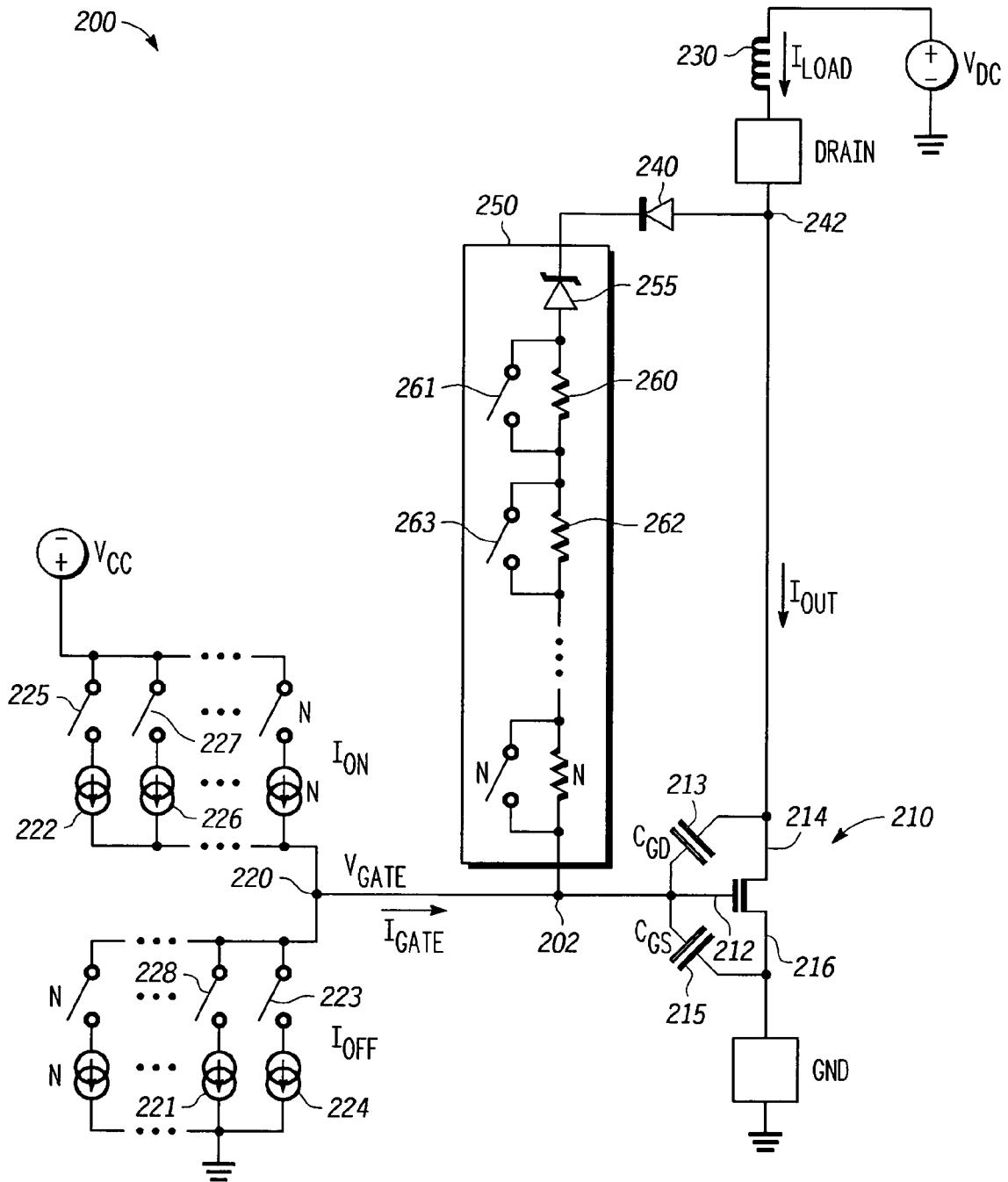


FIG. 2C

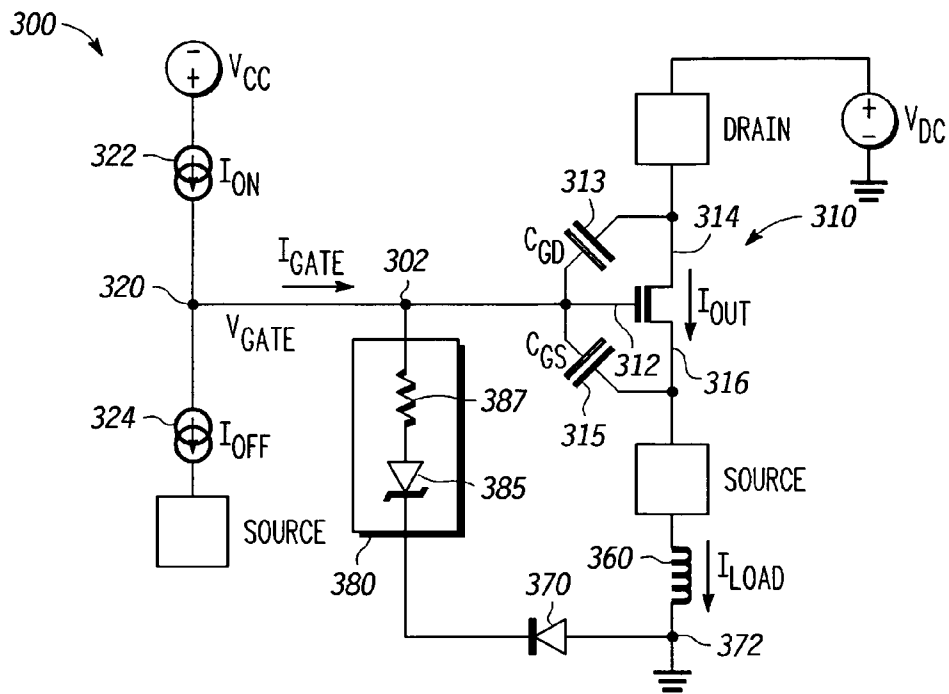


FIG. 3A

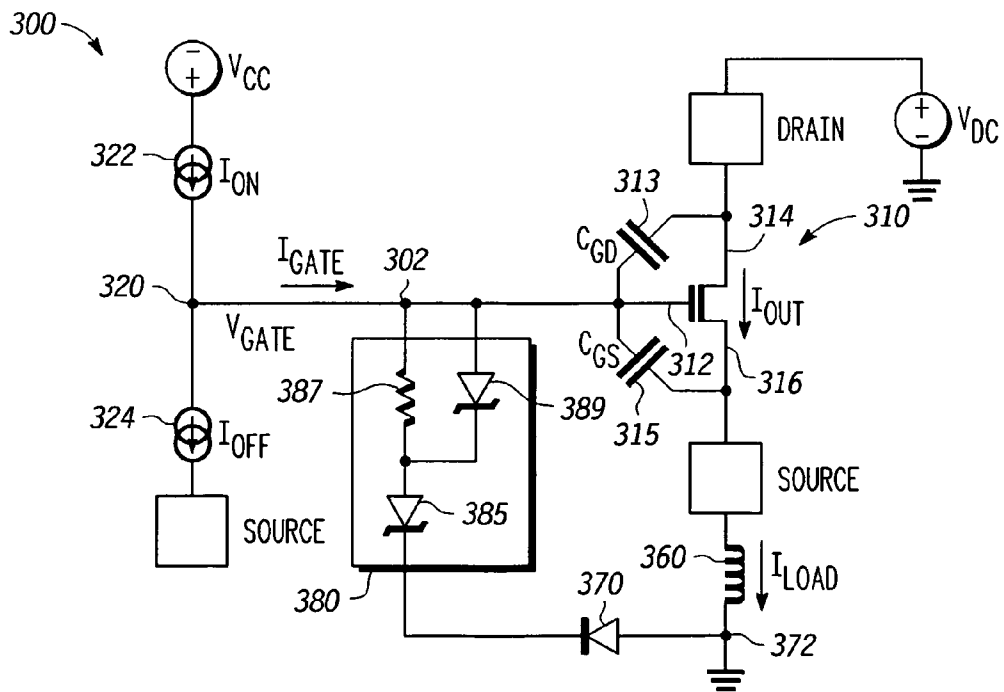


FIG. 3B

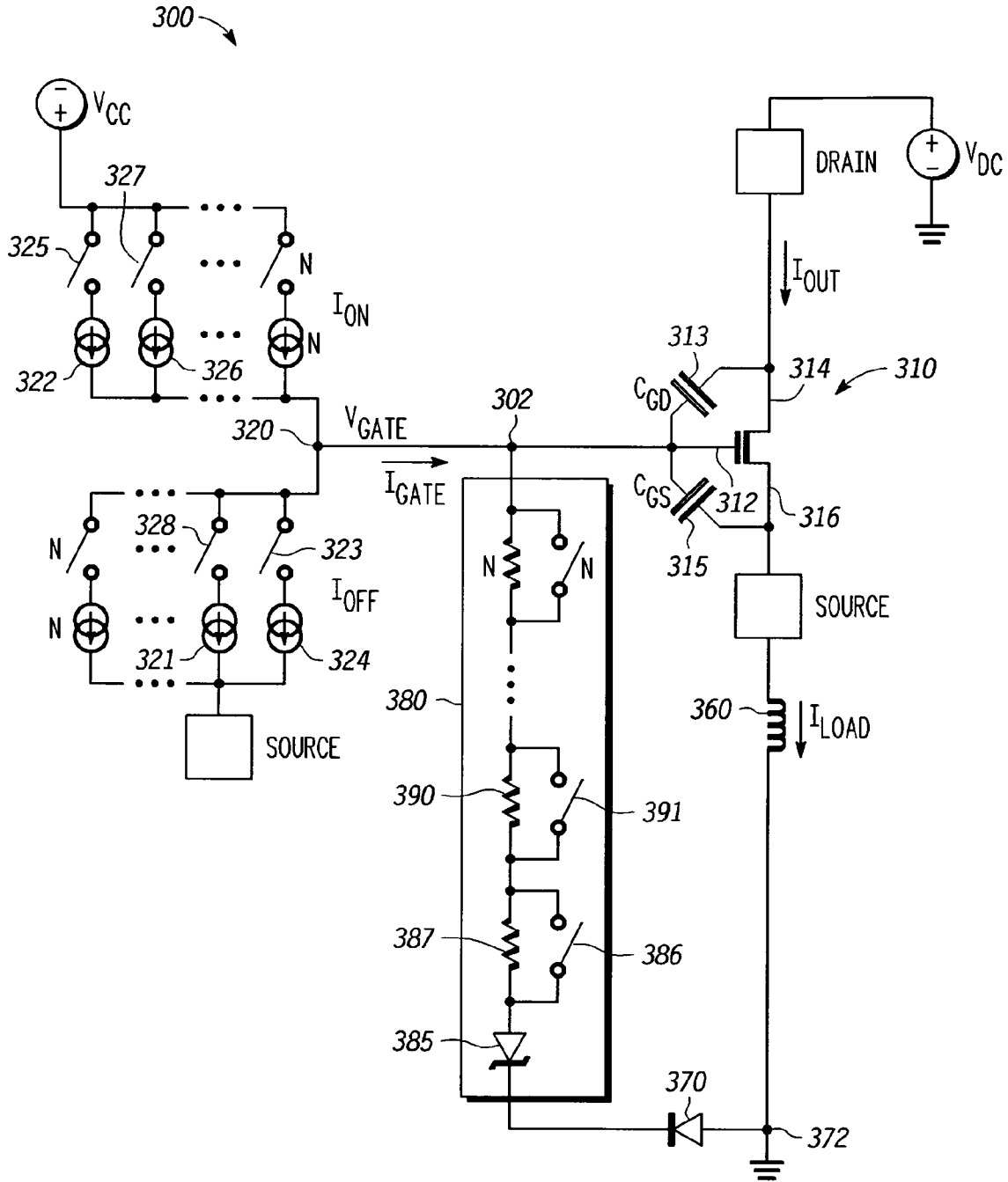


FIG. 3C

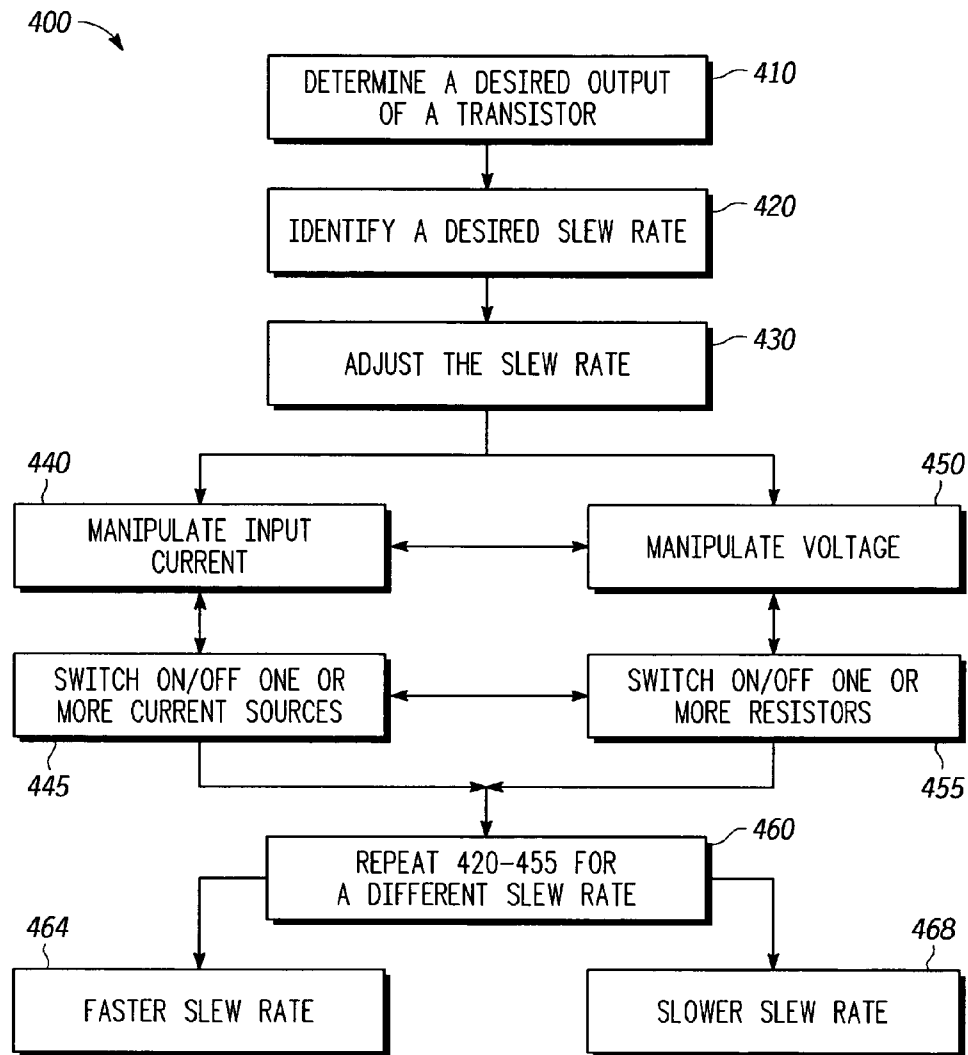


FIG. 4

**SLEW-RATE CONTROL APPARATUS AND
METHODS FOR A POWER TRANSISTOR TO
REDUCE VOLTAGE TRANSIENTS DURING
INDUCTIVE FLYBACK**

FIELD OF THE INVENTION

The present invention generally relates to semiconductor devices, and more particularly relates to power switches.

BACKGROUND OF THE INVENTION

In a power switch, when the transistor driving the inductive load is switched off, the drain voltage of the transistor abruptly increases. This abrupt change in drain voltage often causes conducted or radiated emissions on the output wires leading to the inductive load. The conducted and/or radiated emissions often cause interference in other electronic devices coupled to or proximate to the power switch, which makes the overall system perform less desirably.

Accordingly, it is desirable to provide apparatus and methods that reduce the amount of conducted or radiated emissions from a power switch when the transistor is switched off. In addition, it is desirable to provide apparatus and methods that modify the transition times of voltage in a power switch when the transistor is switched off. Furthermore, other desirable features and characteristics of the present invention will become apparent from the subsequent description of the invention and the appended claims, taken in conjunction with the accompanying drawings and this background of the invention.

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention will hereinafter be described in conjunction with the following drawing figures, wherein like numerals denote like elements, and wherein:

FIG. 1 is a diagram of a prior art power switch;

FIG. 2A is a diagram of one embodiment of a power switch with reduced conducted or radiated emissions;

FIG. 2B is a diagram of the power switch in FIG. 2A with a protection circuit;

FIG. 2C is a diagram of one embodiment of the power switch of FIG. 2A including an adjustable slew rate;

FIG. 3A is a diagram of another embodiment of a power switch with reduced conducted or radiated emissions;

FIG. 3B is a diagram of the power switch in FIG. 3A with a protection circuit;

FIG. 3C is a diagram of one embodiment of the power switch of FIG. 3A including an adjustable slew rate; and

FIG. 4 is a flow diagram of a method to reduce conducted or radiated emissions in a power switch.

DETAILED DESCRIPTION OF THE
INVENTION

The following detailed description is merely illustrative in nature and is not intended to limit the scope or application of possible embodiments. Furthermore, there is no intention to be bound by any expressed or implied theory presented in the preceding technical field, background, brief summary, or the following detailed description.

Various embodiments may be described herein in terms of functional and/or logical block components and various processing steps. It should be appreciated that such block components may be realized by any number of hardware, software, and/or firmware components configured to per-

form the specified functions. For the sake of brevity, conventional techniques and systems related to semiconductor processing, packaging, and semiconductor devices are not treated in exhaustive detail herein.

As discussed above, conventional power switches are unsatisfactory in a number of respects. With reference to FIG. 1A, for example, power switch 100 includes a transistor 110 having a gate 112, a drain 114, and a source 116. Furthermore, transistor 110 inherently includes a gate-drain capacitor (C_{gd}) 113 and a gate-source capacitor (C_{gs}) 115.

Gate 112 is coupled to a current source 122 and a current source 124 via a node 120. In addition, current source 122 is coupled to a voltage source V_{cc} , and current source 124 is coupled to ground.

Often, power switch 100 includes an inductive load 130 coupled in series with a supply voltage V_{dc} , wherein inductive load 130 is also coupled to drain 114. Furthermore, power switch 100 includes a diode 140 coupled to a drain node 142 and to a clamp 150, wherein clamp 150 is also coupled to a gate node 102. As shown, clamp 150 is a zener clamp comprising one or more zener diodes 155. In addition, power switch 100 also provides source 116 coupled to ground.

In operation, transistor 110 is switched “on” when current source 122 is switched on (I_{on}), which causes the gate voltage (V_{gate}) (i.e., the difference between the voltage potential at gate 112 and the voltage potential at source 116) to begin increasing from zero volts. When V_{gate} reaches the threshold voltage (V_{th}) of transistor 110, the drain voltage (V_{drain}) begins decreasing, and until reaching zero volts, the gate current (I_{gate}) begins flowing to charge C_{gd} 113 and C_{gs} 115, wherein the slew rate of the drain voltage, $d(V_{drain})/dt$, is proportional to I_{gate}/C_{gd} . Furthermore, when V_{drain} reaches zero volts, V_{gate} begins increasing above V_{th} , which causes the output current (I_{out}) to begin flowing through inductive element 130 and transistor 110 via the drain-to-source path.

Transistor 110 is switched “off” by switching off current source 122 and switching “on” current source 124 (I_{off}). This causes V_{gate} to begin to decrease. Once V_{gate} decreases to V_{th} , V_{drain} begins increasing as transistor 110 begins to switch off. Inductive element 130 continues to run load current (I_{load}) by forcing V_{drain} above the supply voltage (V_{dc}) until it abruptly reaches its maximum voltage (i.e., the clamp threshold voltage), which holds V_{gate} at V_{th} . This allows transistor 110 to run I_{load} from inductive element 130 until decreasing to zero. When V_{drain} is above V_{dc} , the current in inductive element 130 begins to decrease (i.e., $V_{inductor}=L(di/dt)$). Notably, when the voltage across inductive element 130 is reversed, the current decreases.

As V_{drain} approaches the clamp threshold voltage, current in clamp 150 abruptly changes from running zero current to running I_{gate} . Moreover, as V_{drain} approaches the maximum voltage, an abrupt change in V_{drain} occurs at this point (i.e., abruptly changes from increasing in voltage to a substantially constant voltage). As noted above, these abrupt changes in voltage and current are what causes at least some conducted or radiated emissions that have the potential of interfering with other electronic devices.

With reference now to FIG. 2A, one exemplary embodiment of a power switch 200 with reduced conducted and/or radiated emissions is illustrated. Power switch 200, in one embodiment, includes a transistor 210 (e.g., a field effect transistor or the like) having a gate 212, a drain 214 (and inherently a gate-drain capacitor 213), and a source 216 (and inherently a gate-source capacitor 215).

In addition, power switch **200** includes a node **220** coupled to transistor **210** and coupled to current sources **222** and **224**, wherein current sources **222** and **224** are substantially the same size so that transistor **210** may be properly switched on and off. Furthermore, power switch **200** includes a drain node **242** coupled to drain **214**, an inductive element (e.g., an inductor) **230**, and a diode **240**. In various exemplary embodiments, inductive element **230** includes induction in the range of about 5 millihenries (mH) to about 100 mH. Furthermore, diode **240** is coupled to a clamp **250** including at least one zener diode **255**, wherein clamp **250** is also coupled to a gate node **202**. Zener diode **255** may be any zener diode or device known in the art or developed in the future capable of performing functions similar to a zener diode. Moreover, zener diode **255** may include any suitable voltage threshold (V_{zth}).

In accordance with one exemplary embodiment, clamp **250** includes a resistive element **260** coupled in series with zener diode **255**. Resistive element **260**, in one embodiment, is a resistor. In addition, various embodiments of switch **200** contemplate that resistive element **260** may be any hardware device capable of adding resistance to clamp **250**.

In accordance with one exemplary embodiment, resistive element **260** includes a resistance in the range of about 5 kilohms (k Ω) to about 100 k Ω . Notably, the resistance (R) of resistive element **260** is dependent upon a desired output voltage of clamp **250** and the pull down current of gate **212**. In other words, according to the following formula:

$V_{clamp} = V_z + V_{gs} + V_{diode} + (I_{gate})(R)$, wherein V_z is the voltage of zener diode(s) **255**, V_{gs} is the gate-source voltage, V_{diode} is the voltage of diode **240**, I_{gate} is the pull down current supplied by current source **224**, and R is the resistance of resistive element **260**.

In operation, power switch **200** performs similarly to power switch **100** discussed above. However, the addition of resistive element **260** to clamp **250** reduces conducted or radiated emissions from power switch **200** by increasing the time it takes for V_{drain} to transition from increasing to reaching its maximum voltage and/or the time it takes I_{out} to transition from increasing to decreasing. Specifically, power switch **200** allows current to begin running in clamp **250** prior to V_{drain} reaching the maximum voltage. Moreover, resistive element **260** begins to conduct current when the voltage rises to $V_z + V_{gs} + V_{diode}$. The maximum voltage is reached when V_{drain} equals $V_z + V_{gs} + V_{diode} + (I_{gate})(R)$. The abrupt transition of V_{drain} near the maximum voltage is softened (or rounded) by the addition of resistive element **260**, thus reducing the conducted and/or radiated emissions due to this abrupt voltage change. In one exemplary embodiment of the invention, the transition (or slew rate) forms a function similar to a \cos^2 function.

FIG. 2B is a diagram of an embodiment of power switch **200** having a protection circuit. In the embodiment illustrated in FIG. 2B, clamp **250** also includes an additional zener diode **258** coupled in parallel with resistive element **260**.

Zener diode **258** may be any zener diode or device capable of performing the function of a zener diode known in the art or developed in the future. In one exemplary embodiment, zener diode **258** has a threshold voltage greater than the voltage of resistive element **260** such that damaging excessive current does not flow through resistive element **260** during, for example, a brief electrostatic discharge (ESD) pulse. Moreover, zener diode **258** allows enough I_{gate} to run through clamp **250** when the output is subjected to a high current and/or high voltage transient event (e.g., an ESD pulse).

FIG. 2C is a diagram of one embodiment of power switch **200** including an adjustable slew rate. In accordance with one exemplary embodiment, power switch **200** further comprises at least one additional current source **226** coupled in parallel with current source **222**. Furthermore, a current source switch **227** is coupled to current source **226** such that when switch **227** is "on," additional current is supplied from current supply **226** to transistor **210**, and when "off," additional current is not supplied to transistor **210**. Furthermore, a current source switch **225** is coupled to current source **222** such that when switch **225** is "on," current supplied from current supply **224** may be switched on/off similar to switch **227**. As such, switches **225** and **227** may each be any device known in the art or developed in the future capable of performing such switching functions. As illustrated in FIG. 2C, according to another embodiment, there can be up to N additional current sources and current source switches in parallel with current source **222** and current source switch **225**, where N is an integer number selected according to the requirements of a given power switch implementation.

Furthermore, power switch **200** further comprises at least one additional current source **221** coupled in parallel with current source **224**. In addition, each of current sources **221** and **224** includes a current source switch **228** and **223**, respectively, coupled to it. In one exemplary embodiment, current source **224** is substantially the same size as current source **222**, and current source **221** is substantially the same size as current source **226** so that transistor **210** may be properly switched off by current source **224** and/or **221** (utilizing switch **228** and/or **223**, respectively) when current is supplied by current source **222** and/or **226** (utilizing switch **225** and/or **227**, respectively), respectively. In other words, I_{on} and I_{off} are substantially the same amount of current. Notably, switches **228** and **223** may each be any device known in the art or developed in the future capable of performing such switching functions. Furthermore, as illustrated in FIG. 2C, according to another embodiment, there can be up to N additional current sources and current source switches in parallel with current source **224** and current source switch **223**, where N is an integer number selected according to the requirements of a given power switch implementation.

In addition, clamp **250** comprises at least one additional resistive element **262** coupled in series with zener diode **255** and resistive element **260**. Furthermore, a resistive element switch **261** and a resistive element switch **263** are coupled around resistive elements **260** and **262**, respectively, such that when switch **261** is switched "on," current bypasses resistive element **260** and when switch **261** is switched "off," current flows through resistive element **260**. Similarly, when switch **263** is switched "on," current bypasses resistive element **262** and when switch **263** is switched "off," current flows through resistive element **262**. As such, switches **261** and **263** may each be any device known in the art or developed in the future capable of performing such switching functions. Accordingly, when additional current is supplied by current source **226** (i.e., when switch **227** is "on"), and switches **261** and **263** are "on," power switch **200** can have a different slew rate than the embodiment illustrated above in FIG. 2A. Furthermore, as illustrated in FIG. 2C, according to another embodiment, there can be up to N additional resistive elements (and corresponding resistive element switches) coupled in series with zener diode **255**, where N is an integer number selected according to the requirements of a given power switch implementation.

Accordingly, power switch **200**, in various embodiments, may include any number of additional current sources (and

current source switches) of any size to provide any desired amount of current to transistor **210** (and properly switch off transistor **210**), and may also include any number of additional resistive elements (and resistive element switches) to provide any amount of resistance to clamp **250** such that power switch **200** may include any number of desired slew rates. In accordance with one exemplary embodiment, power switch **200** includes three current sources and current source switches (i.e., I_{on}), three additional current sources and current source switches (i.e., I_{off}), and three resistive elements and resistive element switches such that power switch **200** includes, for example, a slow, a medium, and a fast slew rate.

With reference now to FIG. 3A, another embodiment of a power switch **300** is illustrated. Power switch **300**, in one embodiment includes a transistor **310** having a gate **312**, a drain **314** (and inherently a gate-drain capacitor **313**), and a source **316** (and inherently a gate-source capacitor **315**). In addition, power switch **300** includes a node **320**, a gate node **302**, and a current source **322** similar to node **220**, gate node **202**, and current source **222** discussed above, respectively. Furthermore, power switch **300** includes a current source **324** coupled to source, wherein current source **324** is substantially the same size as current source **322** so that transistor **310** may be properly switched on and off.

In addition, power switch **300** includes an inductive element **360** coupled to transistor **310** and a source node **372**. In various exemplary embodiments, inductive element **360** includes induction in the range of about 5 mH to about 100 mH. Furthermore, source node **372** is coupled to a diode **370**, and diode **370** is coupled to a clamp **380**, wherein clamp **380** is also coupled to gate node **302**. In one embodiment, clamp **380** is a zener clamp comprising at least one zener diode **385**. Moreover, clamp **380**, in one embodiment, includes a resistive element **387** coupled in series with zener diode **385**.

In accordance with one exemplary embodiment, resistive element **387** includes a resistance in the range of about 5 k Ω to about 100 k Ω . Notably, the resistance (R) of resistive element **387** is dependent upon a desired output voltage of clamp **380** and the pull down current of gate **312**. In other words, according to the following formula:

$V_{clamp} = V_z + V_{gs} + V_{diode} + (I_{gate})(R)$, wherein V_z is the voltage of zener diode(s) **385**, V_{gs} is the gate-source voltage, V_{diode} is the voltage of diode **370**, I_{gate} is the pull down current supplied by current source **324**, and R is the resistance of resistive element **387**.

FIG. 3B is a diagram of power switch **300** with a protection circuit. In the embodiment illustrated in FIG. 3B, clamp **380** includes an additional zener diode **389** coupled in parallel with resistive element **387**.

Zener diode **389** may be any zener diode or device capable of performing the function of a zener diode known in the art or developed in the future. In one exemplary embodiment, zener diode **389** includes a threshold voltage greater than the voltage of resistive element **387** such that damaging excessive current does not flow through resistive element **387** during, for example, a brief electrostatic discharge (ESD) pulse. Moreover, zener diode **389** allows enough I_{gate} to run through clamp **380** when the output is subjected to a high current and/or high voltage transient event (e.g., an ESD pulse).

FIG. 3C is a diagram of one embodiment of power switch **300** including an adjustable slew rate. In accordance with one exemplary embodiment, power switch **300** further comprises at least one additional current source **326** coupled in parallel with current source **322**. Furthermore, a current

source switch **327** is coupled to current source **326** such that when switch **327** is "on," additional current supplied from current supply **326** may be provided to transistor **310**, and when "off," additional current is not supplied to transistor **310**. Furthermore, a current source switch **325** is coupled to current source **322** such that when switch **325** is "on," current supplied from current supply **322** may be switched on/off similar to switch **327**. As such, switches **325** and **327** may each be any device known in the art or developed in the future capable of performing such switching functions. As illustrated in FIG. 3C, according to another embodiment, there can be up to N additional current sources and current source switches in parallel with current source **322** and current source switch **325**, where N is an integer number selected according to the requirements of a given power switch implementation.

In addition, power switch **300** further comprises at least one additional current source **321** coupled in parallel with current source **324**. In addition, each of current sources **321** and **324** includes a current source switch **328** and **323**, respectively, coupled to it. In one exemplary embodiment, current source **324** is substantially the same size as current source **322**, and current source **321** is substantially the same size as current source **326** such that transistor **310** may be properly switched off by current source **324** and/or **321** (utilizing switch **328** and/or **323**, respectively) when current is supplied by current source **322** and/or **326** (utilizing switch **325** and/or **327**, respectively), respectively. In other words, I_{on} and I_{off} are substantially the same amount of current. Notably, switches **328** and **323** may each be any device known in the art or developed in the future capable of performing such switching functions. Furthermore, as illustrated in FIG. 3C, according to another embodiment, there can be up to N additional current sources and current source switches in parallel with current source **324** and current source switch **323**, where N is an integer number selected according to the requirements of a given power switch implementation.

Furthermore, clamp **380** comprises at least one additional resistive element **390** coupled in series with zener diode **385** and resistive element **387**. Furthermore, a resistive element switch **386** and a resistive element switch **391** are coupled around resistive elements **387** and **390**, respectively, such that when switch **386** is switched "on," current bypasses resistive element **387** and when switch **386** is switched off," current flows through resistive element **387**. Similarly, when switch **391** is switched "on," current bypasses resistive element **390** and when switch **391** is switched off," current flows through resistive element **390**. Accordingly, when additional current is supplied by current source **326** (i.e., when switch **327** is "on"), and switches **386** and **391** are "on," power switch **300** can have a different slew rate than the embodiment illustrated above in FIG. 3A. As such, switches **386** and **391** may each be any device known in the art or developed in the future capable of performing such switching functions. Furthermore, as illustrated in FIG. 3C, according to another embodiment, there can be up to N additional resistive elements (and corresponding resistive element switches) coupled in series with zener diode **385**, where N is an integer number selected according to the requirements of a given power switch implementation.

Accordingly, power switch **300**, in various embodiments, may include any number of additional current sources (and current source switches) of any size to provide any desired amount of current to transistor **310** (and properly switch off transistor **310**), and may also include any number of additional resistive elements (and resistive element switches) to

provide any amount of resistance to clamp **380** such that power switch **300** may include any number of desired slew rates. In accordance with one exemplary embodiment, power switch **300** includes three current sources and current source switches (i.e., I_{on}), three additional current sources and current source switches (i.e., I_{off}), and three resistive elements and resistive element switches such that power switch **300** includes, for example, a slow, a medium, and a fast slew rate.

FIG. **4** is a flow diagram of a method **400** to reduce conducted or radiated emissions in, for example, a power switch (e.g., power switches **200** or **300**). In accordance with one exemplary embodiment, method **400** initiates by determining a desired output of a transistor (e.g., transistors **210** or **310**) of the power switch (block **410**), and identifying a desired slew rate for the power switch (block **420**).

Next, method **400** includes adjusting the slew rate of the power switch (block **430**). In one exemplary embodiment, adjusting the slew rate comprises manipulating the input current to the transistor from one or more current sources (e.g., current sources **224**, **226**, **324**, or **326**) (block **440**) and/or manipulating a voltage of a clamp (e.g., clamps **250** or **380**) coupled to the transistor (block **450**), wherein manipulating the input current comprises switching on or off one or more current sources to increase or decrease the amount of current supplied to the transistor (block **445**), and manipulating the voltage includes switching on or off one or more resistive elements in the clamp to increase or decrease the amount of voltage in the clamp (block **455**).

In addition, method **400** includes repeating blocks **420** through **455** for a different slew rate (block **460**). In one exemplary embodiment, the different slew rate is a faster slew rate (block **464**), whereas in another embodiment the different slew rate is a slower slew rate (block **468**).

In summary, apparatus to modify a slew rate during inductive flyback is disclosed. In one embodiment, the apparatus comprises a transistor including a gate, a source, and a drain, wherein an inductive load is coupled to the drain. Furthermore, the apparatus includes a plurality of current sources coupled to the gate, wherein a first current source switches on the transistor, and a second current source switches off the transistor. In addition, the apparatus includes a clamp coupled to the gate and to the drain, the clamp comprising a first resistive element to increase a voltage of the clamp when current flows through the clamp, wherein the increased voltage causes the apparatus to include a different slew rate.

In accordance with one embodiment, the clamp comprises a first zener diode and the first zener diode is coupled in series with the first resistive element. In another embodiment, the clamp includes a pre-determined voltage to decrease the slew rate of the apparatus. In yet another embodiment, the pre-determined voltage is determined by at least one of a pre-determined voltage of the at least one zener diode, a pre-determined current of the first current source multiplied by a pre-determined resistance of the first resistive element, and a pre-determined voltage across the gate and source. Moreover, the pre-determined resistance, in an exemplary embodiment, is determined by at least one of a desired voltage output of the transistor and a desired gate pull down current. The clamp, in another embodiment of the apparatus, further comprises a second zener diode coupled in parallel with the first resistive element.

The apparatus, in another exemplary embodiment, further comprises a third current source coupled to the gate and coupled in parallel with the first current source, and a first switch coupled between the third current source and the

gate, wherein the first switch switches on/off the third current source. In yet another embodiment, the clamp further comprises a second resistive element coupled in series with the first resistive element, and a second switch coupled to the clamp, wherein a first side of the second switch of coupled on one side of the second resistive element and a second side of the second switch is coupled to an opposite side of the second resistive element such that when the second switch is open current does not flow through the second resistive element and when the second switch is closed current flows through the second resistive element.

In addition, the disclosure also discusses a second apparatus to modify a slew rate during inductive flyback. In one embodiment, the second apparatus comprises a transistor including a gate, a source, and a drain, wherein an inductive load is coupled to the source. In one embodiment, the apparatus includes a plurality of current sources coupled to the gate, wherein a first current source switches on the transistor and a second current source switches off the transistor. In addition, the apparatus includes a clamp coupled to the gate and to ground, the clamp comprising a first resistive element to increase a voltage of the clamp when current flows through the clamp, wherein the increased voltage causes the apparatus to include a different slew rate.

In accordance with one embodiment, the clamp comprises a first zener diode and the first zener diode is coupled in series with the first resistive element. In another embodiment, the clamp includes a pre-determined voltage to decrease the slew rate of the apparatus. In yet another embodiment, the pre-determined voltage is determined by at least one of a pre-determined voltage of the at least one zener diode, a pre-determined current of the first current source multiplied by a pre-determined resistance of the first resistive element, and a pre-determined voltage across the gate and source. Moreover, the pre-determined resistance, in an exemplary embodiment, is determined by at least one of a desired voltage output of the transistor and a desired gate pull down current. The clamp, in another embodiment of the apparatus, further comprises a second zener diode coupled in parallel with the first resistive element.

The apparatus, in another exemplary embodiment, further comprises a third current source coupled to the gate and coupled in parallel with the first current source, and a first switch coupled between the third current source and the gate, wherein the first switch switches on/off the third current source. In yet another embodiment, the clamp further comprises a second resistive element coupled in series with the first resistive element, and a second switch coupled to the clamp, wherein a first side of the second switch of coupled on one side of the second resistive element and a second side of the second switch is coupled to an opposite side of the second resistive element such that when the second switch is open current does not flow through the second resistive element and when the second switch is closed current flows through the second resistive element.

In addition, the disclosure discusses a method to modify a slew rate during inductive flyback. In one embodiment, the method comprises identifying a desired slew rate for a power transistor, the power transistor comprising a transistor and at least one current source to provide an amount of input current to the transistor, an inductive load, and a clamp coupled to the transistor, wherein the clamp includes at least one zener diode coupled in series with at least one resistive

element, and adjusting a voltage of the clamp to attain the desired slew rate. In accordance with one exemplary embodiment, adjusting the voltage comprises one of adding resistance to the clamp and subtracting resistance from the clamp.

In another exemplary embodiment, the method further comprises adjusting the amount of input current provided to the transistor. In accordance with one embodiment, adjusting the amount of input current comprises one of adding and subtracting input current from at least one additional current source.

While at least one example embodiment has been presented in the foregoing detailed description, it should be appreciated that a vast number of variations exist. It should also be appreciated that the example embodiment or embodiments described herein are not intended to limit the scope, applicability, or configuration of the invention in any way. Rather, the foregoing detailed description will provide those skilled in the art with a convenient road map for implementing the described embodiment or embodiments. It should be understood that various changes can be made in the function and arrangement of elements without departing from the scope of the invention as set forth in the appended claims and the legal equivalents thereof.

We claim:

1. An apparatus featuring inductive flyback slew rate modification, comprising:

a transistor including a gate, a source, and a drain;

an inductive load coupled to the drain;

a plurality of current sources coupled to the gate, wherein a first current source of the plurality of current sources is configurable for switching the transistor ON and a second current source of the plurality of current sources is configurable for switching the transistor OFF; and a clamp coupled between the gate and the drain, wherein the clamp comprises a first resistive element configurable for increasing a voltage of the clamp in response to a current flow through the clamp, a first zener diode coupled in series with the first resistive element, and a second zener diode coupled in parallel with the first resistive element.

2. The apparatus of claim 1, wherein the clamp is configured for a pre-determined voltage to decrease the slew rate of the apparatus.

3. The apparatus of claim 2, wherein the pre-determined voltage is determined by at least one of a pre-determined voltage of the first zener diode, a pre-determined current of the first current source multiplied by a pre-determined resistance of the first resistive element, and a pre-determined voltage across the gate and source.

4. The apparatus of claim 3, wherein the pre-determined resistance is determined by at least one of a desired voltage output of the transistor and a desired gate pull down current.

5. The apparatus of claim 1, further comprising:

a third current source coupled to the gate and coupled in parallel with the first current source;

a first switch coupled between the third current source and the gate, wherein the first switch is configurable for connecting/disconnecting the third current source to the gate;

a fourth current source coupled to the gate and coupled in parallel with the second current source; and

a second switch coupled between the fourth current source, wherein the second switch is configurable for connecting/disconnecting the fourth current source to the gate.

6. The apparatus of claim 5, wherein the clamp further comprises:

a second resistive element coupled in series with the first resistive element; and

a third switch coupled to the clamp, wherein a first side of the third switch is coupled on one side of the second resistive element and a second side of the third switch is coupled to an opposite side of the second resistive element, wherein responsive to the third switch being in an closed state, current is prohibited from flowing through the second resistive element and wherein responsive to the third switch being in an open state, current is enabled to flow through the second resistive element.

7. An apparatus featuring inductive flyback slew rate modification, comprising:

a transistor including a gate, a source, and a drain;

an inductive load coupled to the source;

a plurality of current sources coupled to the gate, wherein a first current source of the plurality of current sources is configurable for switching the transistor ON and a second current source of the plurality of current sources is configurable for switching the transistor OFF; and

a clamp coupled between the gate and ground, wherein the clamp comprises a first resistive element configurable for increasing a voltage of the clamp in response to a current flow through the clamp, a first zener diode coupled in series with the first resistive element, and a second zener diode coupled in parallel with the first resistive element.

8. The apparatus of claim 7, wherein the clamp is configurable for a pre-determined voltage to decrease the slew rate of the apparatus.

9. The apparatus of claim 8, wherein the pre-determined voltage is determined by at least one of a pre-determined voltage of the first zener diode, a pre-determined current of the first current source multiplied by a pre-determined resistance of the first resistive element, and a pre-determined voltage across the gate and source.

10. The apparatus of claim 9, wherein the pre-determined resistance is determined by at least one of a desired voltage output of the transistor and a desired gate pull down current.

11. The apparatus of claim 7, further comprising:

a third current source coupled to the gate and coupled in parallel with the first current source; and

a first switch coupled between the third current source and the gate, wherein the first switch is configurable for connecting/disconnecting the third current source to the gate.

12. The apparatus of claim 11, wherein the clamp further comprises:

a second resistive element coupled in series with the first resistive element; and

a second switch coupled to the clamp, wherein a first side of the second switch is coupled on one side of the second resistive element and a second side of the second switch is coupled to an opposite side of the second resistive element, wherein responsive to the second switch being in an open state, current is prohibited from flowing through the second resistive element and wherein responsive to the second switch being in a closed state, current is enabled to flow through the second resistive element.

11

13. A method to reduce voltage transients during inductive flyback, the method comprising:
identifying a desired slew rate for a power transistor, the power transistor comprising:
a transistor and
at least one current source to provide an amount of input current to the transistor, an inductive load, and a clamp coupled to the transistor, wherein the clamp includes at least one zener diode coupled in series with at least one resistive element and at least one zener diode coupled in parallel with at least one resistive element; and

12

adjusting a voltage of the clamp to attain the desired slew rate.

14. The method of claim 13, wherein:
adjusting the voltage comprises one of adding resistance to the clamp and subtracting resistance from the clamp.

15. The method of claim 13, further comprising:
adjusting the amount of input current provided to the transistor.

16. The method of claim 15, wherein adjusting the amount of input current comprises one of adding and subtracting input current from at least one additional current source.

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